AM3524C

Analog Power

N & P-Channel 20-V (D-S) MOSFET

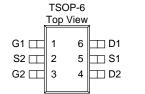
These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

- Low r_{DS(on)} provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe TSOP-6 saves board space
- Fast switching speed
- High performance trench technology

PRODUCT SUMMARY					
V _{DS} (V)	r _{DS(on)} (Ω)	I _D (A)			
20	$0.047 @ V_{GS} = 4.5V$	4.1			
20	0.055 @ V _{GS} = 2.5V	3.8			
-20	$0.079 @ V_{GS} = -4.5V$	-3.2			
-20	$0.110 @ V_{GS} = -2.5V$	-2.7			

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N-Channel MOSFET





P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C UNLESS OTHERWISE NOTED)								
Parameter	Symbol	N-Channel	P-Channel	Units				
Drain-Source Voltage		V _{DS}	20	-20	V			
Gate-Source Voltage			± 8	± 8	v			
	$T_A=25^{\circ}C$	т	4.1	-3.2				
Continuous Drain Current ^a	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	ID	3.3	-2.6	А			
Pulsed Drain Current ^b	I _{DM}	8	-8					
Continuous Source Current (Diode Conduct	Is	1.05	-1.05	А				
	$T_A=25^{\circ}C$	р	1.	W				
Power Dissipation ^a	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	гр	0					
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 te	°C				

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	N-Channel		P-Channel		Unit
			Тур	Max	Тур	Max	Unit
	t <= 10 sec	R _{thJA}	93	110	93	110	°C/W
Maximum Junction-to-Ambient ^a	Steady State		130	150	130	150	

Notes

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- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

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Davamatar	Symptol	Test Conditions			imits		Unit	
Parameter	Symbol	lest Conditions	Ch	Min	Тур	Max	Unit	
Static								
Gate-Threshold Voltage	V _{GS(th)}	$V_{GS} = V_{DS}$, $I_D = 250 \text{ uA}$	N	0.4			v	
	V GS(th)	$V_{GS} = V_{DS}$, $I_D = -250 \text{ uA}$	Р	-0.4			v	
Gate-Body Leakage Current	I _{GSS}	$V_{DS} = 0 V, V_{GS} = 8 V$	N P			100	uA	
, ,	055	$V_{DS} = 0 V, V_{GS} = -8 V$ $V_{DS} = 16 V, V_{GS} = 0 V$	P N			-100		
	-	$V_{DS} = -16 V, V_{GS} = 0 V$ $V_{DS} = -16 V, V_{GS} = 0 V$	P			-1	uA uA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}, T_{I} = 55^{\circ}\text{C}$	N			10		
		$V_{DS} = -16 V, V_{CS} = 0 V, T_{I} = 55 °C$	Р			-10		
On-State Drain Current ^A	I _{D(on)}	$\frac{V_{DS} = 5 V, V_{GS} = 4.5 V}{V_{DS} = -5 V, V_{GS} = -4.5 V}$	N	5			А	
	-D(011)	$V_{DS} = -5 V, V_{GS} = -4.5 V$	P N	-5		0.047	Л	
Drain-Source On-Resistance ^A		$V_{GS} = 4.5 \text{ V}, \text{ ID} = 4.1 \text{ A}$ $V_{GS} = -4.5 \text{ V}, \text{ ID} = -3.2 \text{ A}$	P			0.047	Ω	
	r _{DS(on)}	$V_{GS} = 2.5 V, ID = 3.8 A$	N			0.075		
		$V_{GS} = -2.5 V I_{D} = -2.7 A$	Р			0.110	1	
Forward Tranconductance ^A	α.	$\frac{V_{DS} = 5 \text{ V}, \text{ I}_{D} = 4.1 \text{ A}}{V_{DS} = -5 \text{ V}, \text{ I}_{D} = -3.2 \text{ A}}$ $\frac{I_{S} = 1.05 \text{ A}, V_{GS} = 0 \text{ V}}{I_{S} = -1.05 \text{ A}, V_{GS} = 0 \text{ V}}$	Ν		10		S	
	g _{fs}	$V_{\rm DS} = -5$ V, $I_{\rm D} = -3.2$ A	Р		5			
Diode Forward Voltage ^A	V _{SD}	$I_{\rm S} = 1.05$ A, $V_{\rm GS} = 0$ V	N		0.80		S	
-	35	$I_{\rm S} = -1.05 \text{ A}, V_{\rm GS} = 0 \text{ V}$	Р		-0.83		5	
Dynamic ^b								
Total Gate Charge	Qg	N-Channel	N		7.5			
8-	₹5		P N		3.8			
Gate-Source Charge	Qgs	V_{DS} =15V, V_{GS} =4.5V, I_{D} =4.1A P-Channel	P		0.6		nC	
			N		1.0		-	
Gate-Drain Charge	Q_{gd}	VDS=-15V, VGS=-4.5V, ID=-3.2A	Р		1.5			
T 0 D 1 T			N		5			
Turn-On Delay Time	td(on)	N-Chaneel	Р		5			
Rise Time	tr	V_{DD} =15V, VGS=4.5V, ID=1A,	Ν		12		1	
		$R_{GEN}=15\Omega$,	Р		15		nS	
Turn-Off Delay Time	td(off)	P-Channel	N P		13	ļ	115	
		VDD=-15V, VGS=-4.5V, ID=-1A			20	 	4	
Fall-Time	tf	$R_{GEN}=15\Omega$	N P		7 20		1	

Notes

a. Pulse test: $PW \le 300$ us duty cycle $\le 2\%$.

b. Guaranteed by design, not subject to production testing.

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